BC369



PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.2 A. Sourced from Process 77.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	20	V
V _{CES}	Collector-Base Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	1.5	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		BC369	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

©1997 Fairchild Semiconductor Corporation

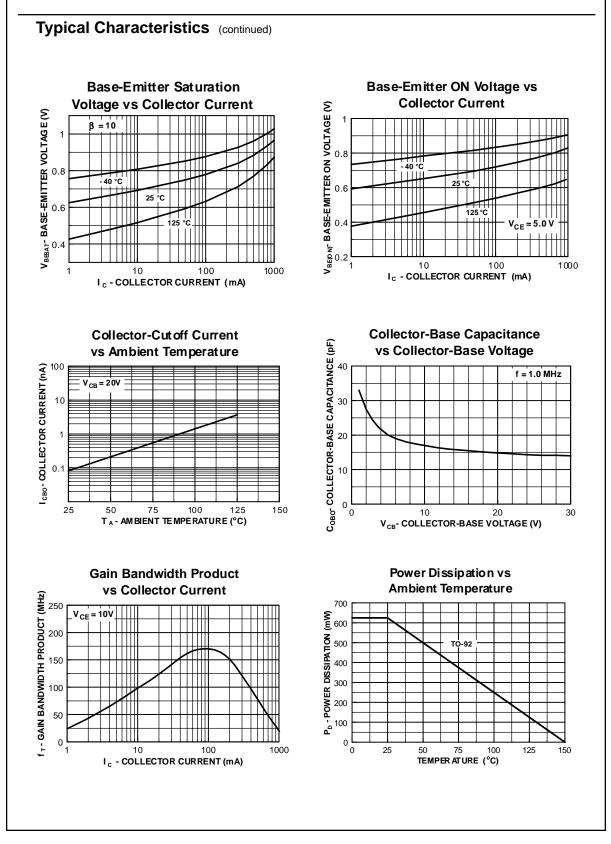
PNP General Purpose Amplifier (continued)

BC369

Symbol	Parameter	Test Conditions	Min	Max	Unit
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	20		V
V _{(BR)CES}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu\text{A}, I_{\rm E} = 0$	25		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 25 \text{ V}, I_E = 0$	0.0	10	μA
СВО		V _{CB} = 25 V, I _E = 0, T _A = 150°C		1.0	mA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		10	μΑ
ON CHAR	ACTERISTICS				
h _{FE}	DC Current Gain	$I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$	50		
- 1°E		$I_{C} = 0.5 \text{ A}, V_{CE} = 1.0 \text{ V}$	85	375	
	Collector Emitter Octure (in 1976)	$I_{\rm C} = 1.0 \text{ A}, V_{\rm CE} = 1.0 \text{ V}$	60	0.5	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0 \text{ A}, I_{\rm B} = 100 \text{ mA}$		0.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$		1.0	V
SMALL SI	IGNAL CHARACTERISTICS				
f _T	Current Gain - Bandwidth Product	$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 5.0 \text{ V},$	45		MHz
	ages (V) and currents (A) are negative polarity for PNP to a current sector polarity for PNP to current sector polarity for PNP to a current sector polarity fo	f = 35 MHz transistors.	<u> </u>		<u> </u>
Туріса	al Characteristics	transistors.	<u> </u>		<u> </u>
Туріса	al Characteristics ypical Pulsed Current Gain	transistors.			-
Typica	al Characteristics	transistors.			-
Typica	al Characteristics ypical Pulsed Current Gain	transistors.			-
Typica	al Characteristics ypical Pulsed Current Gain vs Collector Current	transistors.			-
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	Transistors. Collector- S Voltage vs $\beta = 10$ $\beta = 10$ $\beta = 10$			-
	al Characteristics ypical Pulsed Current Gain vs Collector Current	Transistors. Collector- S Voltage vs $\beta = 10$ $\beta = 10$ $\beta = 10$			-
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	Transistors. Collector- S Voltage vs $\beta = 10$ $\beta = 10$ $\beta = 10$		or Curren	-
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	Transistors. Collector- S Voltage vs $\beta = 10$ $\beta = 10$ $\beta = 10$		25°C	t
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	Transistors. Collector- S Voltage vs $\beta = 10$ $\beta = 10$ $\beta = 10$		or Curren	-
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$	Transistors. Collector- S Voltage vs $\beta = 10$ $\beta = 10$ $\beta = 10$		25°C	t
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$ $25 \degree C$ $-40 \degree C$ 0.1 $125 \degree C$ 0.1	transistors. Collector- Voltage vs $\beta = 10$ $\beta = 10$	Collecto	or Curren	t
	al Characteristics ypical Pulsed Current Gain vs Collector Current V _{CE} = 5.0V 125 °C -40 °C -40 °C	transistors. Collector- Voltage vs $\beta = 10$ $\beta = 10$		or Curren	t 125 °C
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$ $25 \degree C$ $-40 \degree C$ 0.1 $125 \degree C$ 0.1	transistors. Collector- Voltage vs $\beta = 10$ $\beta = 10$	Collecto	or Curren	t 125 °C
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$ $25 \degree C$ $-40 \degree C$ 0.1 $125 \degree C$ 0.1	transistors. Collector- Voltage vs $\beta = 10$ $\beta = 10$	Collecto	or Curren	125°C
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$ $25 \degree C$ $-40 \degree C$ 0.1 $125 \degree C$ 0.1	transistors. Collector- Voltage vs $\beta = 10$ $\beta = 10$	Collecto	or Curren	125°C
	al Characteristics ypical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$ $25 \degree C$ $-40 \degree C$ 0.1 $125 \degree C$ 0.1	transistors. Collector- Voltage vs $\beta = 10$ $\beta = 10$	Collecto	or Curren	t 125 °C

BC369

PNP General Purpose Amplifier (continued)



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM BottomlessTM CoolFETTM $CROSSVOLT^{TM}$ DOMETM E²CMOSTM EnSignaTM FACTTM FACT Quiet SeriesTM FAST ® FASTr[™] GlobalOptoisolator[™] GTO[™] HiSeC[™] ISOPLANAR[™] MICROWIRE[™] OPTOLOGIC[™] OPTOPLANAR[™] PACMAN[™] POP[™] PowerTrench® QFET™ QS™ QT Optoelectronics™ Quiet Series™ SILENT SWITCHER® SMART START™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SyncFET[™] TinyLogic[™] UHC[™] VCX[™]

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Product Status	Definition
Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
	In Design First Production Full Production

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death a

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Downloaded from Arrow.com.